Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Description (continued)

Despite the low power consumption of the circuitry in the A139x, the features required to produce a highly accurate linear Hall-effect IC have not been compromised. Each BiCMOS monolithic circuit integrates a Hall element, improved temperature-compensating circuitry to reduce the intrinsic sensitivity drift of the Hall element, a small-signal high-gain amplifier, and proprietary dynamic offset cancellation circuits. End of line, post-packaging, factory programming allows precise control of device sensitivity and offset.

These devices are available in a small 2.0×3.0 mm, 0.75 mm nominal height micro-leaded package (MLP/DFN). It is Pb (lead) free, with 100% matte tin leadframe plating.

Selection Guide

Part Number	Sensitivity (mV/G, Typ.)	Package	Packing ¹
A1391SEHLT-T ²	1.25	DFN/MLP 2×3 mm; 0.75 mm nominal height	7-in. reel, 3000 pieces/reel
A1392SEHLT-T ²	2.50	DFN/MLP 2x3 mm; 0.75 mm nominal height	7-in. reel, 3000 pieces/reel
A1393SEHLT-T ²	5	DFN/MLP 2×3 mm; 0.75 mm nominal height	7-in. reel, 3000 pieces/reel
A1395SEHLT-T ²	10	DFN/MLP 2×3 mm; 0.75 mm nominal height	7-in. reel, 3000 pieces/reel



¹Contact Allegro[™] for additional packing options.

²Allegro products sold in DFN package types are not intended for automotive applications.

Absolute Maximum Ratings*

Characteristic	Symbol	Notes	Rating	Unit
Supply Voltage	V _{CC}		8	V
Reverse-Supply Voltage	V _{RCC}		-0.1	V
Ratiometric Supply Reference Voltage	V _{REF}		7	V
Reverse-Ratiometric Supply Reference Voltage	V _{RREF}		-0.1	V
Logic Supply Voltage	V _{SLEEP}	(V _{CC} > 2.5 V)	32	V
Reverse-Logic Supply Voltage	VRSLEEP		-0.1	V
Output Voltage	V _{OUT}		V _{CC} + 0.1	V
Reverse-Output Voltage	V _{ROUT}		-0.1	V
Operating Ambient Temperature	T _A	RangeS	-20 to 85	°C
Junction Temperature	T _J (MAX)		165	°C
StorageTemperature	T _{stg}		-65 to 170	°C

*All ratings with reference to ground

Pin-out Diagram



Terminal List Table

Pin	Name	Function
1	VCC	Supply
2	OUT	Output
3	GND	Ground
4	GND	Ground
5	SLEEP	Toggle sleep mode
6	VREF	Supply for ratiometric reference



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Device Characteristics Tables

Characteristic	Symbol	Test Conditions	Min.	Typ.1	Max.	Units
Supply Voltage	V _{CC}		2.5	_	3.5	V
Nominal Supply Voltage	V _{CCN}		-	3.0	-	V
Supply Zener Clamp Voltage	V _{CCZ}	I _{CC} = 7 mA, T _A = 25°C	6	8.3	-	V
Ratiometric Reference Voltage ²	V _{REF}		2.5	-	V _{CC}	V
Ratiometric Reference Zener Clamp Voltage	V _{REFZ}	I _{VREF} = 3 mA, T _A = 25°C	6	8.3	-	V
SLEEP Input Voltage			-0.1	_	V _{CC} + 0.5	V
SLEEP Input Threshold	V _{INH}	For active mode	-	0.45 × V _{CC}	-	V
	V _{INL}	For sleep mode	-	0.20 × V _{CC}	-	V
Ratiometric Reference Input Resistance	D	$V_{SLEEP} > V_{INH}$, $V_{CC} = V_{CCN}$, $T_A = 25^{\circ}C$	250	-	-	kΩ
	R _{REF}	$V_{SLEEP} < V_{INL,} V_{CC} = V_{CCN,}$ $T_A = 25^{\circ}C$	_	5	-	MΩ
Chopper Stabilization Chopping Frequency	f _C	$V_{CC} = V_{CCN}, T_A = 25^{\circ}C$	-	200	-	kHz
SLEEP Input Current	I _{SLEEP}	V_{SLEEP} = 3 V, V_{CC} = V_{CCN}	-	1	-	μA
Supply Current ³	las	$V_{SLEEP} < V_{INL,} V_{CC} = V_{CCN,}$ $T_A = 25^{\circ}C$	-	0.025	-	mA
	I _{CC}	$V_{SLEEP} > V_{INH}$, $V_{CC} = V_{CCN,}$ $T_A = 25^{\circ}C$	_	3.2	-	mA
Quiescent Output Power Supply Rejection ⁴	PSR _{VOQ}	f _{AC} < 1 kHz	-	-60	-	dB

ELECTRICAL CHARACTERISTICS valid through full operating ambient temperature range, unless otherwise noted

¹Typical data are for initial design estimations only, and assume optimum manufacturing and application conditions, such as $T_A = 25^{\circ}$ C. Performance may vary for individual units, within the specified maximum and minimum limits.

 2 Voltage applied to the VREF pin. Note that the V_{REF} voltage must be less than or equal to V_{cc}. Degradation in device accuracy will occur with applied voltages of less than 2.5 V.

 3 If the VREF pin is tied to the VCC pin, the supply current would be I_{CC} + V_{REF} / R_{REF}

 4 $\rm f_{AC}$ is any AC component frequency that exists on the supply line.



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

OUTPUT CHARACTERISTICS: valid through full operating ambient temperature range, unless otherwise noted

Characteristic	Symbol		Test Conditions	Min.	Typ.1	Max.	Units
Linear Output Voltage	V _{OUTH}	$V_{CC} = V$	$V_{\rm CCN}, V_{\rm REF} \le V_{\rm CC}$	_	V _{REF} – 0.1	-	V
Range	V _{OUTL}	$V_{CC} = V$	$V_{\rm CCN}, V_{\rm REF} \le V_{\rm CC}$	_	0.1	-	V
Maximum Voltage Applied to Output	V _{OUTMAX}	V _{SLEEP}	o < V _{INL}	_	-	V _{CC} + 0.1	V
		A1391	$T_A = 25^{\circ}C, V_{CC} = V_{REF} = V_{CCN}$	_	1.25	_	mV/G
Sensitivity ²	Sens	A1392	$T_A = 25^{\circ}C, V_{CC} = V_{REF} = V_{CCN}$	_	2.50	-	mV/G
Sensitivity	Selis	A1393	$T_A = 25^{\circ}C, V_{CC} = V_{REF} = V_{CCN}$	_	5	-	mV/G
		A1395	$T_A = 25^{\circ}C, V_{CC} = V_{REF} = V_{CCN}$	_	10	-	mV/G
Quiescent Output	V _{OUTQ}	$T_{A} = 25$	5°C, B = 0 G	_	0.500 × V _{REF}	-	V
Output Resistance ³	R _{OUT}	f _{out} = 1 kHz, V _{SLEEP} > V _{INH} , active mode		_	20	-	Ω
		$f_{out} = 1$	kHz, V _{SLEEP} < V _{INL} , sleep mode	_	4M	-	Ω
Output Load Resistance	RL	Output	to ground	15	-	-	kΩ
Output Load Capacitance	CL	Output	to ground	_	-	10	nF
Output Bandwidth	BW	-3 dB V _{CC} = 1	point, V _{OUT} = 1 V _{pp} sinusoidal, V _{CCN}	-	10	-	kHz
		1391	C _{bypass} = 0.1 μF, BW _{externalLPF} = 2 kHz	-	6	12	mV _{pp}
			$C_{bypass} = 0.1 \ \mu F$, no load	_	-	20	mV _{pp}
Noise ^{4,5}	\	1392	$C_{bypass} = 0.1 \ \mu F$, no load	_	-	40	mV _{pp}
	V _n 1	1393	C _{bypass} = 0.1 μF, BW _{externalLPF} = 2 kHz	_	12	24	mV _{pp}
			$C_{bypass} = 0.1 \ \mu F$, no load	_	-	40	mV _{pp}
		1395	$C_{bypass} = 0.1 \ \mu F$, no load	_	-	80	mV _{pp}

¹Typical data are for initial design estimations only, and assume optimum manufacturing and application conditions, such as T_A = 25°C. Performance may vary for individual units, within the specified maximum and minimum limits.

²For V_{REF} values other than V_{REF} = V_{CCN}, the sensitivity can be derived from the following equation: $K \times V_{REF}$, where K = 0.416 for the A1391, K = 0.823 for the A1392, K = 1.664 for the A1393, and K = 3.328 for the A1395.

³f _{OUT} is the output signal frequency.

⁴Noise specification includes digital and analog noise.

⁵Values for BW_{externalLPF} do not include any noise resulting from noise on the externally supplied VREF voltage.



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

OUTPUT TIMING CHARACTERISTICS¹: $T_A = 25^{\circ}C$

Characteristic	Symbol	Test Conditions	Min.	Typ. ²	Max.	Units
Power-On Time ³	t _{PON}		_	40	60	μs
Power-Off Time ⁴	t _{POFF}		_	1	_	μs

¹See figure 1 for explicit timing delays.

²Typical data are for initial design estimations only, and assume optimum manufacturing and application conditions, such as $T_A = 25^{\circ}$ C. Performance may vary for individual units, within the specified maximum and minimum limits.

³Power-On Time is the elapsed time after the voltage on the SLEEP pin exceeds the active mode threshold voltage, V_{INH}, until the time the device output reaches 90% of its value.

⁴Power-Off Time is the duration of time between when the signal on the \overline{SLEEP} pin switches from HIGH to LOW and when I_{CC} drops to under 100 µA. During this time period, the output goes into the HIGH impedance state.

MAGNETIC CHARACTERISTICS: T_A = 25°C

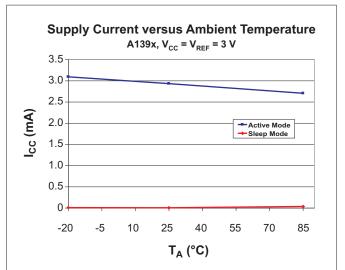
Characteristic	Symbol	Test Conditions	Min.	Тур.*	Max.	Units
Ratiometry	ΔV _{OUTQ(ΔV)}		-	100	-	%
Ratiometry	∆Sens _(∆V)		-	100	-	%
Positive Linearity	Lin+		-	100	-	%
Negative Linearity	Lin–		-	100	-	%
Symmetry	Sym		-	100	-	%

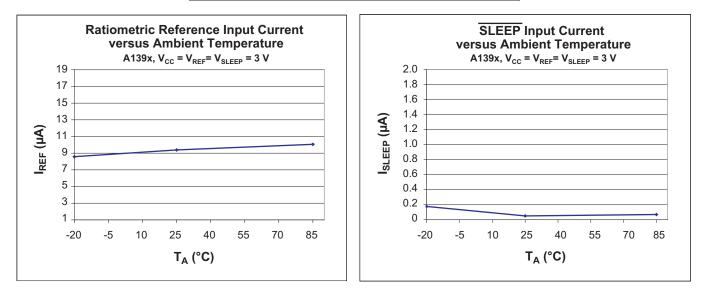
*Typical data are for initial design estimations only, and assume optimum manufacturing and application conditions, such as T_A = 25°C. Performance may vary for individual units, within the specified maximum and minimum limits.



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode



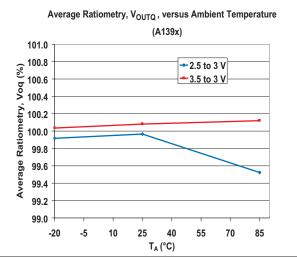


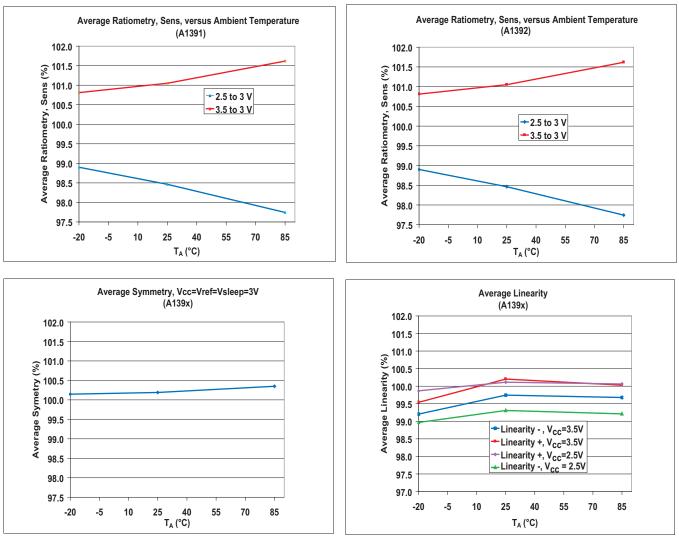




Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Magnetic Characteristic Data





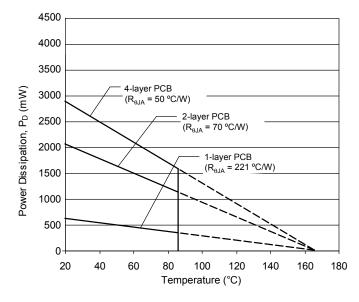


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Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

THERMAL CHARACTERISTICS may require derating at maximum conditions, see application information

Characteristic	Symbol	Test Conditions	Min.	Units
		1-layer PCB with copper limited to solder pads	221	°C/W
Package Thermal Resistance	$R_{\theta JA}$	2-layer PCB with 0.6 in. ² of copper area each side, connected by thermal vias	70	°C/W
		4-layer PCB based on JEDEC standard	50	°C/W



Power Dissipation versus Ambient Temperature



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Characteristics Definitions

Ratiometric. The A139x devices feature ratiometric output. The quiescent voltage output and sensitivity are proportional to the ratiometric supply reference voltage.

The percent ratiometric change in the quiescent voltage output is defined as:

$$\Delta V_{\text{OUTQ}(\Delta V)} = \frac{\Delta V_{\text{OUTQ}(\text{V}_{\text{REF}})} \div \Delta V_{\text{OUTQ}(3V)}}{V_{\text{REF}} \div 3 \text{ V}} \times 100 \%$$
(1)

and the percent ratiometric change in sensitivity is defined as:

$$\Delta \text{Sens}_{(\Delta V)} = \frac{\Delta \text{Sens}_{(V_{\text{REF}})} \div \Delta \text{Sens}_{(3V)}}{V_{\text{REF}} \div 3 \text{ V}} \times 100\%$$
(2)

Linearity and Symmetry. The on-chip output stage is designed to provide a linear output with maximum supply voltage of V_{CCN} . Although application of very high magnetic fields will not damage these devices, it will force the output into a non-linear region. Linearity in percent is measured and defined as

$$Lin+ = \frac{V_{OUT(+B)} - V_{OUTQ}}{2(V_{OUT(+B/2)} - V_{OUTQ})} \times 100\%$$
 (3)

$$Lin = \frac{V_{OUT(-B)} - V_{OUTQ}}{2(V_{OUT(-B/2)} - V_{OUTQ})} \times 100\%$$
(4)

and output symmetry as

$$Sym = \frac{V_{OUT(+B)} - V_{OUTQ}}{V_{OUTQ} - V_{OUT(-B)}} \times 100\%$$
(5)



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Device Low-Power Functionality

A139x are low-power Hall-effect sensor ICs that are perfect for power sensitive customer applications. The current consumption of these devices is typically 3.2 mA, while the device is in the active mode, and less than 25 μ A when the device is in the sleep mode. Toggling the logic level signal connected to the SLEEP pin drives the device into either the active mode or the sleep mode. A logic low sleep signal drives the device into the sleep mode, while a logic high sleep signal drives the device into the active mode.

In the case in which the VREF pin is powered before the VCC pin, the device will not operate within the specified limits until the supply voltage is equal to the reference voltage. When the device is switched from the sleep mode to the active mode, a time defined by t_{PON} must elapse before the output of the device is

valid. The device output transitions into the high impedance state approximately t_{POFF} seconds after a logic low signal is applied to the \overline{SLEEP} pin (see figure 1).

If possible, it is recommended to power-up the device in the sleep mode. However, if the application requires that the device be powered on in the active mode, then a 10 k Ω resistor in series with the SLEEP pin is recommended. This resistor will limit the current that flows into the SLEEP pin if certain semiconductor junctions become forward biased before the ramp up of the voltage on the VCC pin. Note that this current limiting resistor is not required if the user connects the SLEEP pin directly to the VCC pin. The same precautions are advised if the device supply is powered-off while power is still applied to the SLEEP pin.

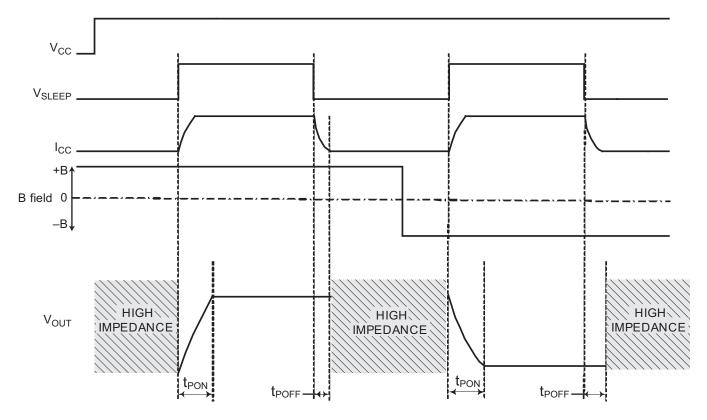


Figure 1. A139x Timing Diagram



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Device Supply Ratiometry Application Circuit

Figures 2 and 3 present applications where the VCC pin is connected together with the VREF pin of the A139x. Both pins are connected to the battery, Vbat2. In this case, the device output will be ratiometric with respect to the battery voltage.

The only difference between these two applications is that the $\overline{\text{SLEEP}}$ pin in figure 2 is connected to the Vbat2 potential, so the device is always in the active mode. In figure 3, the $\overline{\text{SLEEP}}$ pin is toggled by the microprocessor; therefore, the device is selectively and periodically toggled between active mode and sleep mode.

In both figures, the device output is connected to the input of an A-to-D converter. In this configuration, the converter reference voltage is Vbat1.

It is *strongly recommended* that an external bypass capacitor be connected, in close proximity to the A139x device, between the VCC and GND pins of the device to reduce both external noise and noise generated by the chopper-stabilization circuits inside of the A139x.

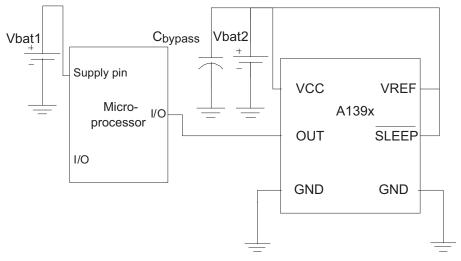


Figure 2. Application circuit showing sleep mode disabled and output ratiometric to the A139x supply.

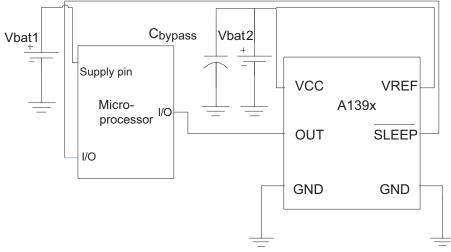


Figure 3. Application circuit showing microprocessor-controlled sleep mode and output ratiometric to the A139x supply.



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Application Circuit with User-Configurable Ratiometry

In figures 4 and 5, the microprocessor supply voltage determines the ratiometric performance of the A139x output signal. As in the circuits shown in figures 2 and 3, the device is powered by the Vbat2 supply, but in this case, ratiometry is determined by the microprocessor supply, Vbat1.

The $\overline{\text{SLEEP}}$ pin is triggered by the output logic signal from the microprocessor in figure 5, while in figure 4, the $\overline{\text{SLEEP}}$ pin is connected to the device power supply pin. Therefore, the device as configured in figure 4 is constantly in active mode, while the device as configured in figure 5 can be periodically toggled

between the active and sleep modes.

The capacitor C_{filter} is optional and can be used to prevent possible noise transients from the microprocessor supply reaching the device reference pin, VREF.

It is *strongly recommended* that an external bypass capacitor be connected, in close proximity to the A139x device, between the VCC and GND pins of the device to reduce both external noise and noise generated by the chopper-stabilization circuits inside of the A139x.

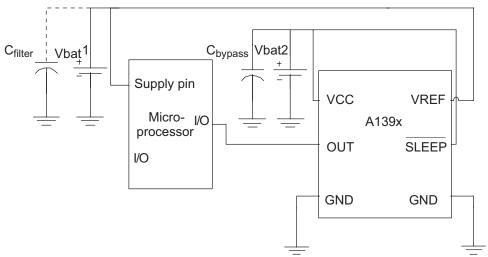


Figure 4. Application circuit showing ratiometry of V_{REF} . Sleep mode is disabled and the VREF pin is tied to the microprocessor supply.

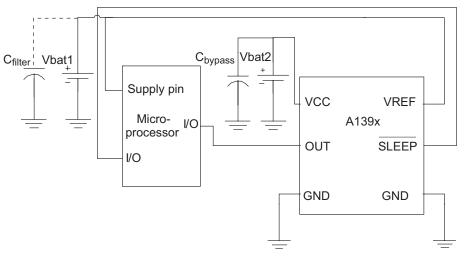
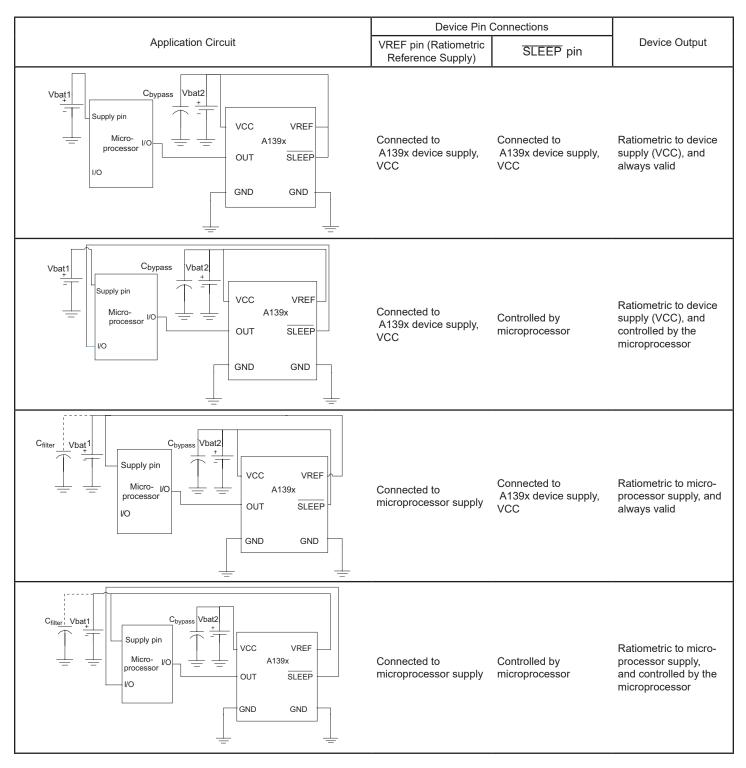


Figure 5. Application circuit showing device reference pin, VREF, tied to microprocessor supply. The device sleep mode also is controlled by the microprocessor.



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Summary of Single-Device Application Circuits





Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Application Circuit with Multiple Hall Devices and a Single A-to-D Converter

Multiple A139x devices can be connected to a single microprocessor or A-to-D converter input. In this case, a single device is periodically triggered and put into active mode by the microprocessor. While one A139x device is in active mode, all of the other A139x devices must remain in sleep mode. While these devices are in sleep mode, their outputs are in a high-impedance state. In this circuit configuration, the microprocessor reads the output of one device at a time, according to microprocessor input to the SLEEP pins.

When multiple device outputs are connected to the same microprocessor input, pulse timing from the microprocessor (for example, lines A1 through A4 in figure 6) must be configured to prevent more than one device from being in the awake mode at any given time of the application. A device output structure can be damaged when its output voltage is forced above the device supply voltage by more than 0.1 V.

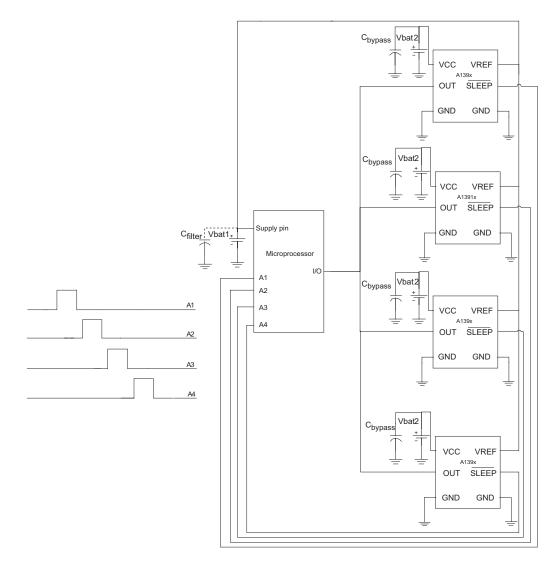


Figure 6. Application circuit showing multiple A139x devices, controlled by a single microprocessor.

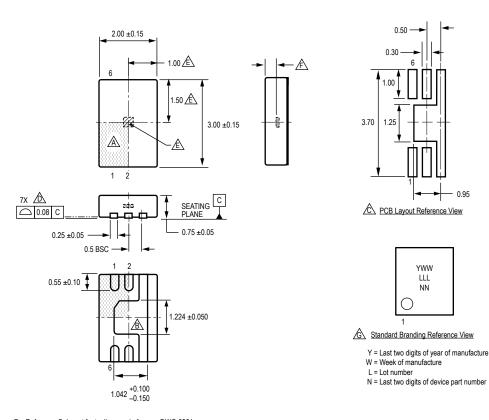


Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

0.95

YWW LLL

NN



Package EH, 6-pin MLP/DFN

For Reference Only, not for tooling use (reference DWG-2861; reference JEDEC MO-229WCED, Type 1) Dimensions in millimeters Exact case and lead configuration at supplier discretion within limits shown

- A Terminal #1 mark area
- Exposed thermal pad (reference only, terminal #1 identifier appearance at supplier discretion)
- ∕∆ Reference land pattern layout;
 - All pads a minimum of 0.20 mm from all adjacent pads; adjust as necessary to meet application process requirements and PCB layout tolerances; when mounting on a multilayer PCB, thermal vias at the exposed thermal pad land can improve thermal dissipation (reference EIA/JEDEC Standard JESD51-5)
- Coplanarity includes exposed thermal pad and terminals
- Hall Element (not to scale); U.S. customary dimensions controlling
- Active Area Depth, 0.32 mm NOM
- Branding scale and appearance at supplier discretion



Micropower 3 V Linear Hall-Effect Sensor ICs with Tri-State Output and User-Selectable Sleep Mode

Revision History

Number	Date	Description
7	October 26, 2011	Update Selection Guide
8	February 13, 2019	Minor editorial updates
9	February 28, 2020	Minor editorial updates

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